

## PATENT ABSTRACTS OF JAPAN

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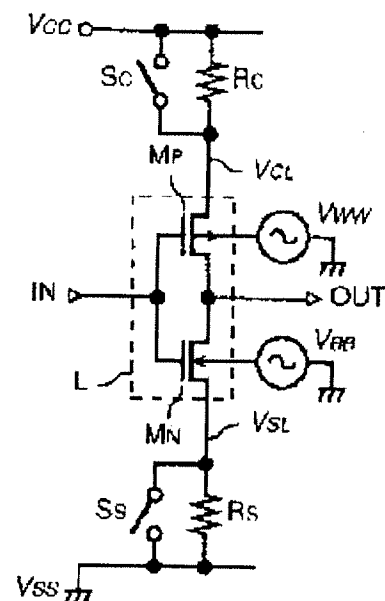
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## (54) SEMICONDUCTOR INTEGRATED CIRCUIT

(57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor integrated circuit high in operating speed and low in power consumption.

**SOLUTION:** Means (switches  $S_c$  and  $S_s$  and resistance  $R_c$  and  $R_s$ ) for controlling the current supply of large and small currents are inserted between an MOS transistor circuit (L) and power sources ( $V_{cc}$  and  $V_{ss}$ ), to make substrate potential variable. Thus, it is possible to select a small current and obtain a low power consumption property when it is in a standby state and to select a large current and obtain rapidity when it operates.



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